Amendments to the Claims:

Claims 1-18. (Previously canceled)

19. (Currently Amended) A method of fabricating a transistor source/drain contact between adjacent transistor gate structures comprising:

depositing an amorphous carbon filler material at least in a region between the adjacent transistor gate structures;

planarinzing the amorphous carbon filler material such that the planarized amorphous carbon filler material remains only between the adjacent transistor gate structures;

removing the planarized amorphous carbon filler material with a process having a removal selectivity to nitride greater than 40:1 to form a contact opening; and

depositing a conductive material in the contact opening.

20. (Currently Amended) A method of fabricating a transistor source/drain contact between adjacent transistor gate structures having nitride sidewall spacers comprising:

depositing an amorphous carbon filler material at least in a region between the adjacent transistor gate structures;

planarinzing the amorphous carbon filler material such that the planarized amorphous carbon filler material remains only between the adjacent transistor gate structures;

removing the planarized filler material with a process having a removal selectivity to nitride greater than 40:1 to form a contact opening having an aspect ratio greater than about 5:1; and

depositing a conductive material in the contact opening.

21. (Currently Amended) A method of fabricating a transistor source/drain connection between adjacent transistor gate structures comprising:

depositing an amorphous carbon filler material at least in a region between the adjacent transistor gate structures;

planarizing the amorphous carbon filler material such that the planarized amorphous carbon filler material remains only between the adjacent transistor gate structures;

selectively dry developing the planarized amorphous carbon filler material in the region between the adjacent transistor gate structures to form a contact opening; and

depositing a polysilicon material in the contact opening.

Please add claims 22 – 33 as recited below.

22. (Currently Added) The method of claim 19, wherein the removing of the planarized amorphous carbon comprises fusion strip/wet clean processing utilizing an O_2 fusion strip, followed by a wet chemistry clean.

23. (Currently Added) The method of claim 22 wherein the wet chemistry clean comprises tungsten ammonium hydroxide/hydrogen peroxide mixture (WAPM) chemistry.

24. (Currently Added) The method of claim 22 wherein the wet chemistry clean comprises ammonium hydroxide/hydrogen peroxide mixture (APM) chemistry.

25. (Currently Added) The method of claim 22 wherein the wet chemistry clean comprises hydrofluoric acid (HF) chemistry.

26. (Currently Added) The method of claim 20, wherein the removing of the planarized amorphous carbon comprises fusion strip/wet clean processing utilizing an O_2 fusion strip, followed by a wet chemistry clean.

27. (Currently Added) The method of claim 26 wherein the wet chemistry clean comprises tungsten ammonium hydroxide/hydrogen peroxide mixture (WAPM) chemistry.

28. (Currently Added) The method of claim 26 wherein the wet chemistry clean comprises ammonium hydroxide/hydrogen peroxide mixture (APM) chemistry.

29. (Currently Added) The method of claim 26 wherein the wet chemistry clean comprises hydrofluoric acid (HF) chemistry.

30. (Currently Added) The method of claim 21, wherein the removing of the planarized amorphous carbon comprises fusion strip/wet clean processing utilizing an O_2 fusion strip, followed by a wet chemistry clean.

31. (Currently Added) The method of claim 30 wherein the wet chemistry clean comprises tungsten ammonium hydroxide/hydrogen peroxide mixture (WAPM) chemistry.

32. (Currently Added) The method of claim 30 wherein the wet chemistry clean comprises ammonium hydroxide/hydrogen peroxide mixture (APM) chemistry.

33. (Currently Added) The method of claim 30 wherein the wet chemistry clean comprises hydrofluoric acid (HF) chemistry.